

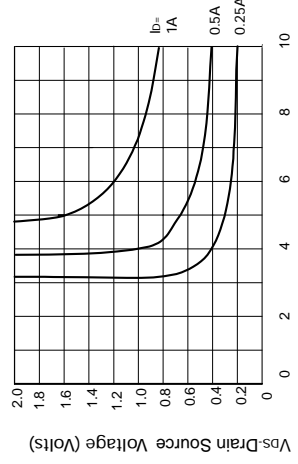
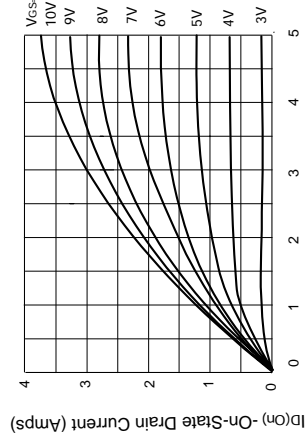


**THE DATASHEET OF
ZVN2106ASTZ**



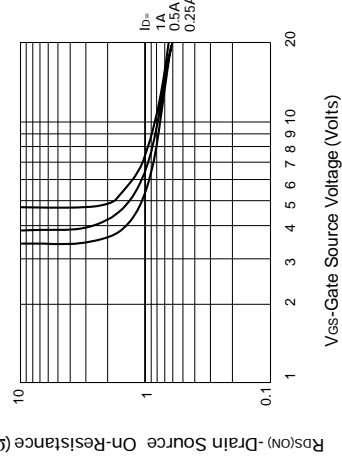
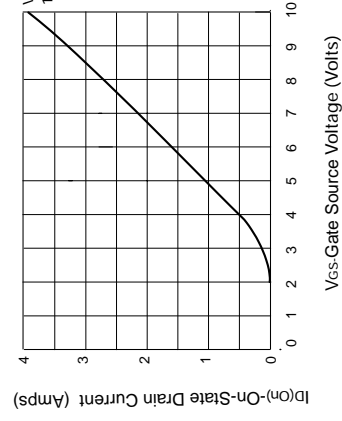
ZVN2106A

TYPICAL CHARACTERISTICS



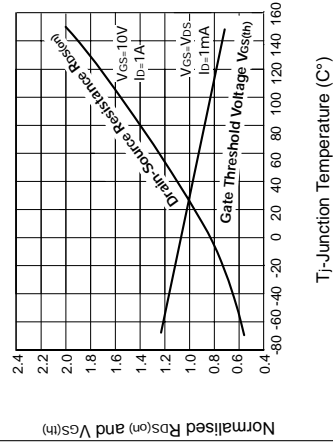
Saturation Characteristics

Voltage Saturation Characteristics



Transfer Characteristics

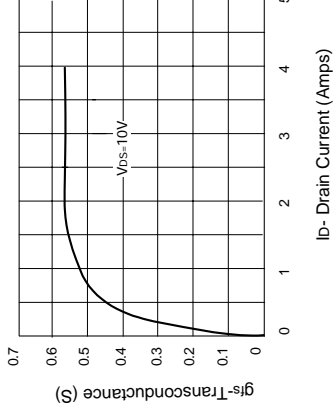
On-resistance v gate-source voltage



T_J -Junction Temperature ($^{\circ}C$)

Normalized $R_{DS(on)}$ and $V_{GS(th)}$ vs Temperature

Transconductance v drain current



N-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

ISSUE 2 – MARCH 94

FEATURES

- * 60 Volt V_{DS}
- * $R_{DS(on)} = 2\Omega$

ABSOLUTE MAXIMUM RATINGS

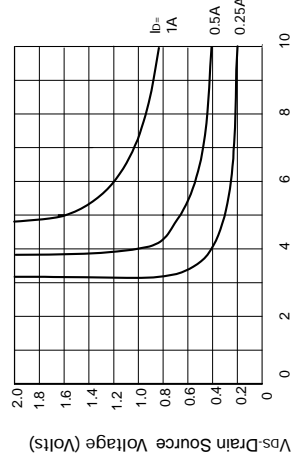
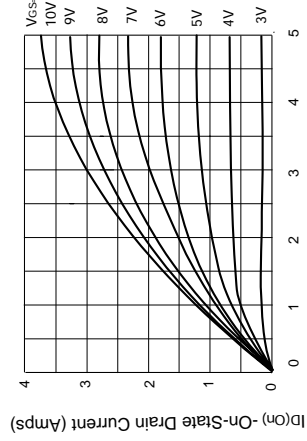
PARAMETER
Drain-Source Voltage
Continuous Drain Current at $T_{amb}=25^{\circ}C$
Pulsed Drain Current
Gate Source Voltage
Power Dissipation at $T_{amb}=25^{\circ}C$
Operating and Storage Temperature Range

ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL
Drain-Source Breakdown Voltage	BV_{DSS}
Gate-Source Threshold Voltage	$V_{GS(th)}$
Gate-Body Leakage	I_{GSS}
Zero Gate Voltage Drain Current	I_{DSS}
On-State Drain Current(1)	$I_{D(on)}$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$
Forward Transconductance (1)(2)	g_{fs}
Input Capacitance (2)	C_{iss}
Common Source Output Capacitance (2)	C_{oss}
Reverse Transfer Capacitance (2)	C_{riss}

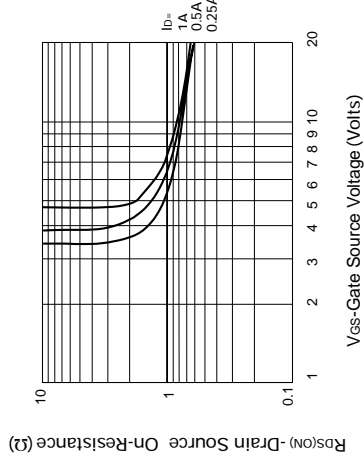
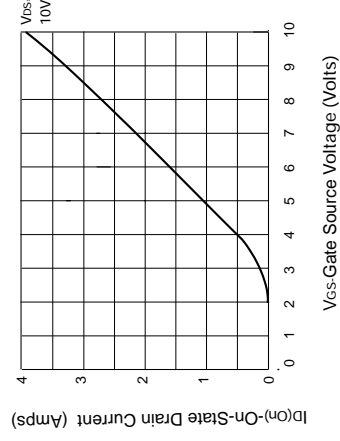
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TYPICAL CHARACTERISTICS



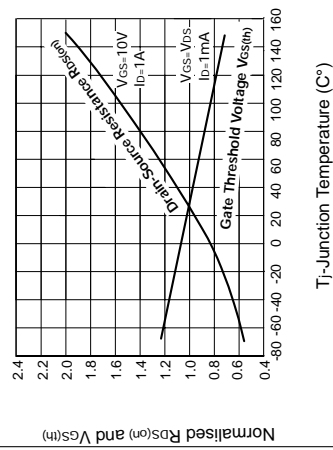
Saturation Characteristics

Voltage Saturation Characteristics



Transfer Characteristics

On-resistance v gate-source voltage

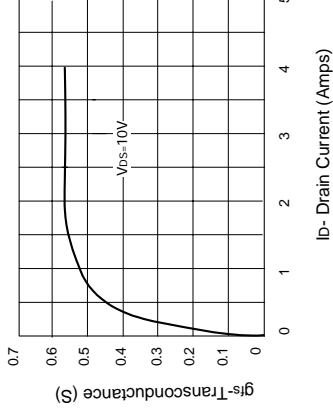


T_J -Junction Temperature ($^{\circ}C$)

Normalized $R_{DS(on)}$ and $V_{GS(th)}$ vs Temperature

I_D - Drain Current (Amps)

Transconductance v drain current



N-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

ISSUE 2 - MARCH 94

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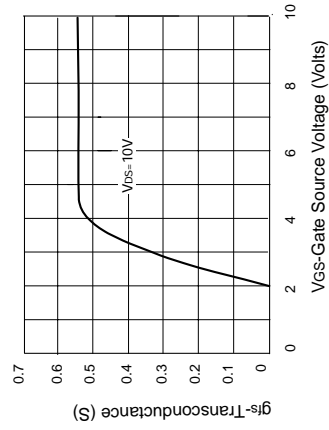
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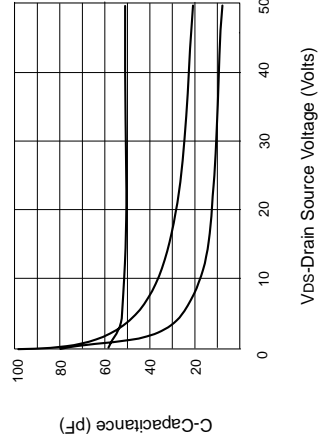
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ZVN2106A

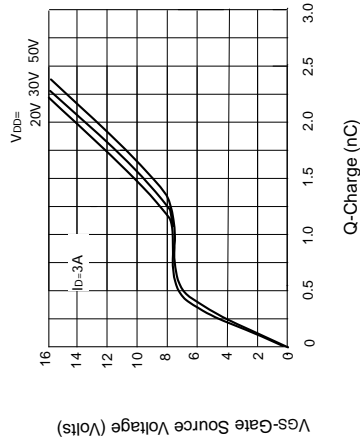
TYPICAL CHARACTERISTICS



Transconductance v gate-source voltage





Capacitance v drain-source voltage



Gate charge v gate-source voltage

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